

AMENDMENTS TO THE CLAIMS

1 (Canceled).

2 (Currently amended). ~~The semiconductor laser device as claimed in claim 1A~~
semiconductor laser device, which is provided with an active layer and a first clad layer on a
substrate and provided with a ridge section constructed of a second clad layer and upper layers
including a cap layer on the first clad layer,

the upper layer protruding in both widthwise directions beyond the second clad layer,
providing a step of not smaller than 0.13 μm between the upper layers and the second clad layer,
wherein

a current constriction layer is provided on both sides of the ridge section, and a portion of
the current constriction layer, the portion being located outside a portion brought in contact with the
ridge section and having surfaces formed flatly, is formed to have a thickness smaller than a
thickness of the second clad layer of the ridge section.

3 (Currently amended). The semiconductor laser device as claimed in claim 1~~2~~, wherein
a portion of the current constriction layer brought in contact with the ridge section has a
thickness of not smaller than half a thickness of the second clad layer of the ridge section.

4 (Currently amended). The semiconductor laser device as claimed in claim 1~~2~~, wherein
the substrate is an inclined substrate.

5 (Original). A semiconductor laser device manufacturing method comprising the steps of:
forming at least an active layer, a first clad layer, a second clad layer and upper layers
including a cap layer on a substrate; and

forming a ridge section comprised of the second clad layer and the upper layers by
subjecting the second clad layer and the upper layers to dry etching and subsequently to wet etching.

6 (Original). The semiconductor laser device manufacturing method as claimed in claim 5,
wherein

a step is formed between the upper layers and the second clad layer by making the upper
layers protrude in both widthwise directions beyond the second clad layer by wet etching.